

Silicon NPN Epitaxial Planar Transistor (Complement to type 2SA1216)

Application : Audio and General Purpose

■ Absolute maximum ratings (Ta=25°C)

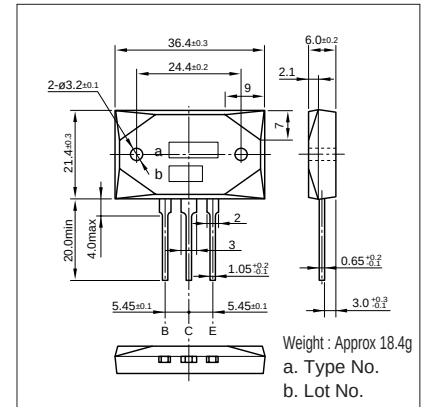
Symbol	2SC2922	Unit
V _{CB0}	180	V
V _{CEO}	180	V
V _{EB0}	5	V
I _C	17	A
I _B	5	A
P _C	200(Tc=25°C)	W
T _J	150	°C
T _{stg}	-55 to +150	°C

■ Electrical Characteristics (Ta=25°C)

Symbol	Conditions	2SC2922	Unit
I _{CBO}	V _{CB} =180V	100max	μA
I _{EBO}	V _{EB} =5V	100max	μA
V _{(BR)CEO}	I _C =25mA	180min	V
h _{FE}	V _{CE} =4V, I _C =8V	30min*	
V _{CE(sat)}	I _C =8A, I _B =0.8A	2.0max	V
f _r	V _{CE} =12V, I _E =-2A	50typ	MHz
COB	V _{CB} =10V, f=1MHz	250typ	pF

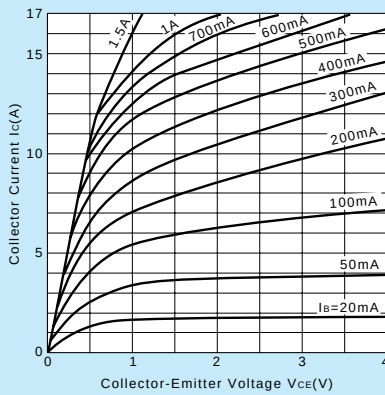
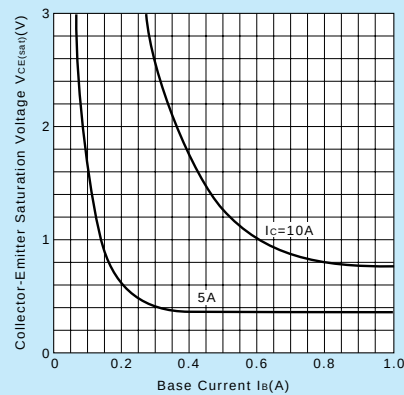
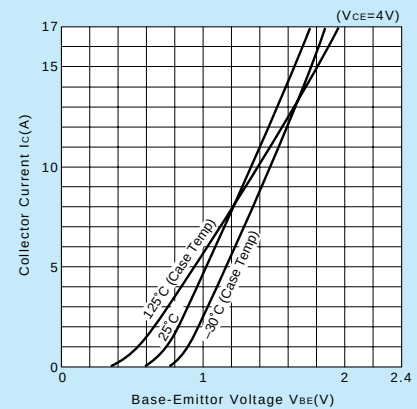
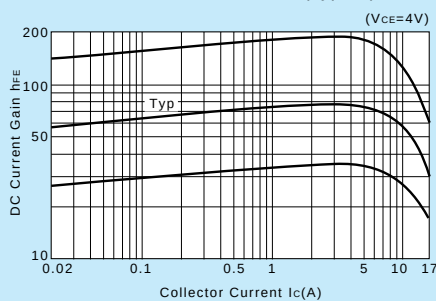
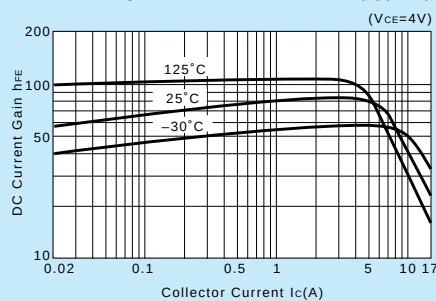
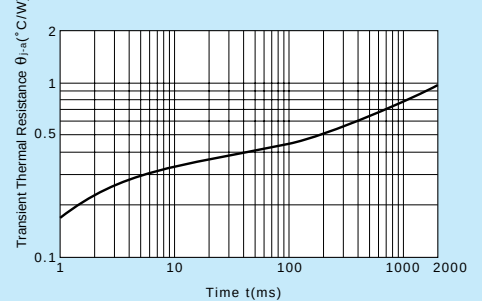
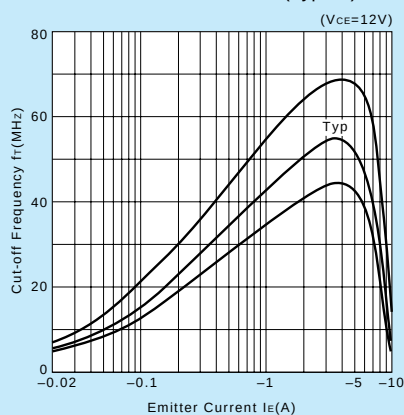
*h_{FE} Rank $\bar{O}$ (30 to 60), Y(50 to 100), P(70 to 140), G(90 to 180)

External Dimensions MT-200

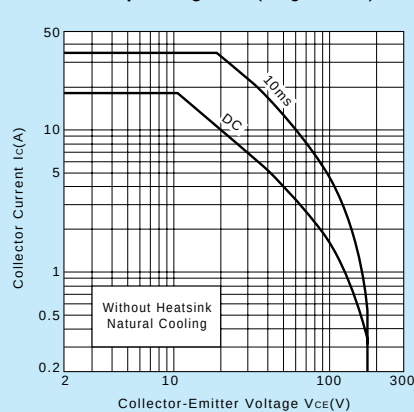


■ Typical Switching Characteristics (Common Emitter)

V _{CC} (V)	R _L (Ω)	I _C (A)	V _{B2} (V)	I _{B1} (A)	I _{B2} (A)	t _{on} (μs)	t _{stg} (μs)	t _f (μs)
40	4	10	-5	1	-1	0.2typ	1.3typ	0.45typ

I_C-V_{CE} Characteristics (Typical)V_{CE(sat)}-I_B Characteristics (Typical)I_C-V_{BE} Temperature Characteristics (Typical)h_{FE}-I_C Characteristics (Typical)h_{FE}-I_C Temperature Characteristics (Typical)θ_{JA}-t Characteristicsf_T-I_E Characteristics (Typical)

Safe Operating Area (Single Pulse)

P_C-T_a Derating